

PNP Transistor KSB1098 datasheet

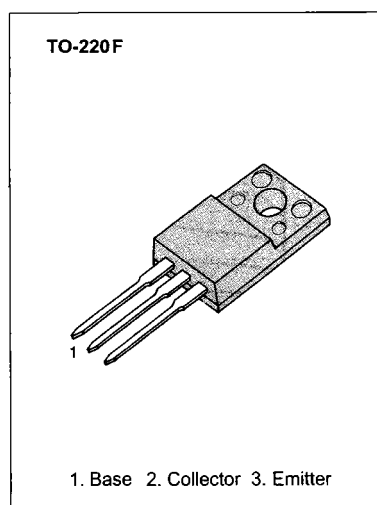
LOW FREQUENCY POWER AMPLIFIER LOW SPEED SWITCHING INDUSTRIAL USE

• Complement to KSD1589

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Characteristic	Symbol	Rating	Unit
Collector Base Voltage	V _{CB0}	-100	V
Collector Emitter Voltage	V _{CEO}	-100	V
Emitter Base Voltage	V _{EB0}	-7	V
Collector Current (DC)	I _C	-5	A
*Collector Current (Pulse)	I _C	-8	A
Base Current	I _B	-0.5	A
Collector Dissipation (Ta=25°C)	P _C	2	W
Collector Dissipation (Tc=25°C)	P _C	20	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55~150	°C

*PW≤10ms, Duty Cycle≤50%



ELECTRICAL CHARACTERISTICS (Ta=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I _{CB0}	V _{CB} = -100V, I _E = 0			-1	μA
Emitter Cutoff Current	I _{EB0}	V _{EB} = -5V, I _C = 0			-3	mA
*DC Current Gain	h _{FE1}	V _{CE} = -2V, I _C = -3A	2000		15K	
	h _{FE2}	V _{CE} = -2V, I _C = -5A	500			
*Collector Emitter Saturation Voltage	V _{CE(sat)}	I _C = -3A, I _B = -3mA			-1.5	V
*Base Emitter Saturation Voltage	V _{BE(sat)}	I _C = -3A, I _B = -3mA			-2	V
Turn On Time	t _{on}	I _C = -3A, R _L = 17Ω		0.5		μs
Storage Time	t _{stg}	I _{B1} = -I _{B2} = -3mA		1		μs
Fall Time	t _f	V _{CC} = -50V		1		μs

*Pulse Test: PW≤350μs, Duty Cycle≤2% Pulsed

h_{FE}(1) CLASSIFICATION

Classification	R	O	Y
h _{FE1}	2000~5000	3000~7000	5000~15000

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